1SS119

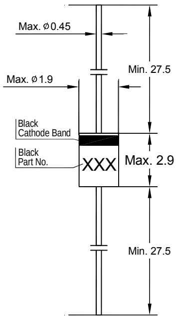
Silicon Epitaxial Planar Switching Diode

Features

- Low capacitance
- Short reverse recovery time

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	35	V
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Peak Forward Current	I_{FM}	450	mA
Non-Repetitive Peak Forward Surge Current (t = 1 s)	I_{FSM}	1	A
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_{stg}	- 65 to + 175	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	0.8	V
Reverse Current at V_R = 30 V	I_R	0.1	µA
Total Capacitance at V_R = 1 V, f = 1 MHz	C_{tot}	3	pF
Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, R_L = 50 Ω	t_{rr}	3.5	ns

Fig.1-Forward current Vs. Forward voltage

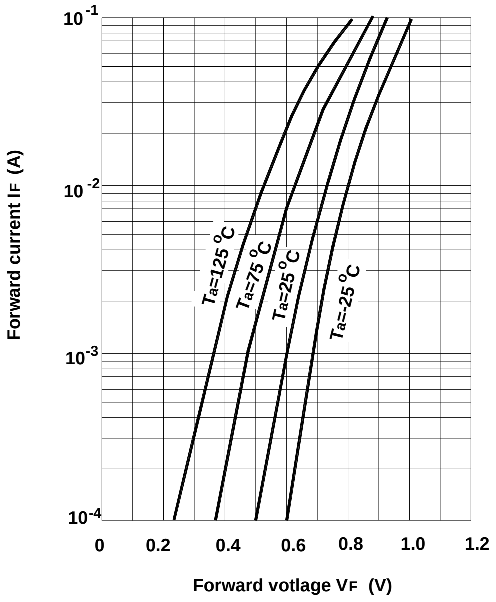


Fig.2- Reverse current Vs. Reverse voltage

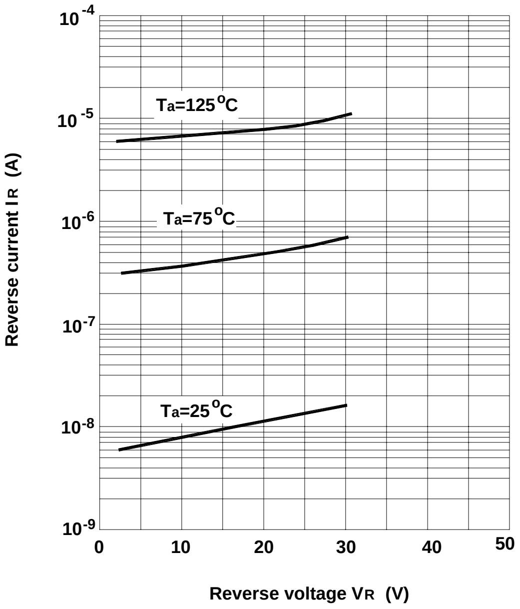


Fig.3- Capacitance Vs. Reverse voltage